

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	3756	(438/303 or 438/305 or 438/306 or 438/307 or 438/595).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:21
S2	652838	spacer or side\$1wall	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:22
S3	24707	ldd or light\$3 adj5 drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:31
S4	548359	nitride or "sin" or "si.sub.3n.sub.4" or "si.sub.3 n.sub.4"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:24
S5	281840	"si3n4" or oxide near3 (aluminum or tantalum or titanium or zirconium or hafnium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:27
S6	177955	"al.sub.2o.sub.3" or "al.sub.2 o.sub.3" or "al2o3" or "tao.sub."\$2 or "tio.sub."\$2 or "zro.sub."\$2 or "hfo.sub."\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:30
S7	875040	S4 or S5 or S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/04 12:26
S8	58644	high adj3 (di\$1electric or k) or high\$1k	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:32

S9	31630	S2 same S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:32
S10	1980	S2 same S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:32
S11	32718	S9 or S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:33
S12	5302	S11 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:33
S13	4787519	anneal\$3 or heat\$4 or thermal\$2 adj3 treat\$5 or activat\$4 with (impurity or dopant)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:36
S14	1009008	gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:37
S15	3678	S12 and S13 and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:43
S16	1411649	mos or mos\$1fet or mis or mis\$fet or fet or cmos\$3 or field adj5 effect adj5 (transistor or device)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:46

S17	3281	S15 and S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:47
S18	19798	(S2 with S7) or (S2 with S8)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:48
S19	2730	S18 and S3 and S13 and S14 and S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:50
S20	26797	first adj3 S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:58
S21	26679	second adj3 S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:59
S22	3154	S20 and S21 and S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:51
S23	717	S22 and S3 and S13 and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:52
S24	936	S18 and (S20 or S21) and S3 and S13 and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:54

S25	852	S24 and S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:54
S26	95328	first with S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:59
S27	90079	second with S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 11:59
S28	1541	S26 and S27 and S18 and S3 and S13 and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 12:01
S29	1380	S28 and S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 12:01
S30	429233	(si or silicon) adj4 (oxide or dioxide) or "sio.sub.2" or "sio2" or "sio.sub."\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/04 12:27
S31	13397	S30 with S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 12:04
S32	6397	(second or third) same S2 same S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 12:08

S33	12144	first same S2 same (S7 or S8)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:30
S34	988	S32 and S33 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 12:08
S35	691	S34 and S13 and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 12:09
S36	623557	first same (S2 or insulat\$3 or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:37
S37	24758	light\$3 adj5 (source\$1drain or drain\$1source) or S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:33
S38	2952	S36 same S37 same implant\$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:34
S39	601919	(second or third) same (S2 or insulat\$3 or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:39
S40	11025	S39 same (source or drain or source\$1drain or drain\$1source) same implant\$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:37

S41	2130	S38 and S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:37
S42	64405	first same (S2 or insulat\$3 or dielectric) same (S7 or S8)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:38
S43	1129	S41 and S42	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:38
S44	42646	(second or third) same (S2 or insulat\$3 or dielectric) same S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:39
S45	660	S43 and S44	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:39
S46	473	S45 and (anneal\$4 or heat\$4 or thermal\$2 adj3 treat\$5 or activat\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:42